

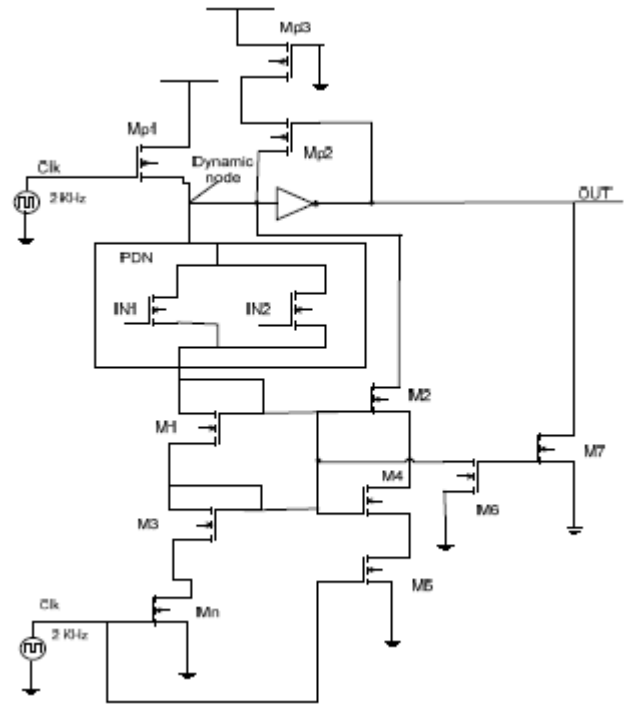
**Figure 3: Footer domino logic**

NMOS pull down network increases the gate to source voltage. So that sub-threshold current increases the charging of dynamic node [8].

#### 4. Pervious Domino Logic Circuit

The domino logic scheme is shown in Fig.4[4]. In this circuit in place of footer transistor current mirror circuits are used in stack. Purpose of current mirror circuits is such that, if any noise signal occurs at M1 it will be leak to ground via M4 and M5. Transistors M3 and M4 also forms current mirror, due to both current mirror circuits gate to source voltage of NMOS pull down network decreases rapidly. This effect is called as stacking effect. The purpose of M4 and M5 in the proposed circuit to create stacking effect, due to which voltage drop across M2 reduces [9]-[10].

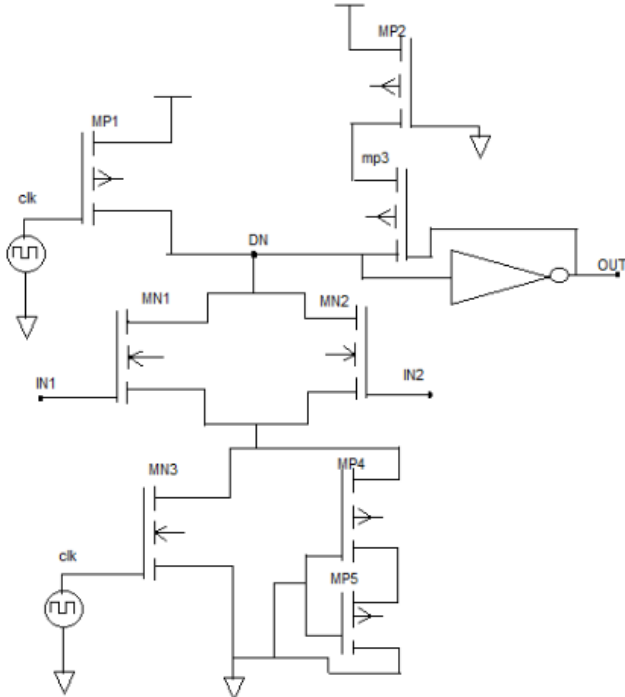
The presence of current mirrors in the proposed circuit causes increase in delay. To overcome this problem size (W/L ratio) of PDN should be increased. Because of stacking effect circuit dissipates power and becomes less noise robust. In this proposed circuit there will be voltage drop in evaluation phase due to stacked current mirrors. Due to negative Vgs, there will be exponential reduction in subthreshold current in the circuit. In order to improve power-delay product more and more, size of PMOS transistor should be four times that of NMOS transistor in inverter circuit at the output node. Purpose of transistor Mp3 is to provide strong vdd to the lower PMOS Mp2, Because PMOS transistor are used to provide strong one logic to the circuit.



**Figure 4: Pervious domino logic**

#### 5. Proposed Domino Logic Circuit

The proposed domino logic scheme is shown in Fig.5. In this circuit in place of current mirror circuits are used the stack of PMOS transistor in footer logic. The modified circuit of domino logic contains the stack of PMOS transistor in footer logic, the schematic and configuration of this approach work in a manner so it can reduce the leakage to ground and indirectly reduces the power dissipation novel low-leakage-power design is described. The transistors are held in reverse body bias. This reverse body biasing increases their threshold. This increased threshold voltage results in low leakage current and hence low leakage power. As we know the leakage current is the main cause of power dissipation we have reduce the leakage power using a stack of PMOS transistor in Footer circuits. PMOS degrades the low logic level. As we know that static power is relative to the voltage apply, through the reduced voltage the power decreases and we get the advantage of less degradation of logic. This approach contains another advantage during off mode if we increase the threshold voltage PMOS Transistors in Footer Circuits.



**Figure 5:** Modified circuit using PMOS Stack in footer circuit

The transistors are held in reverse body bias. Because as result their threshold is high, higher threshold voltage causes low leakage current and therefore low leakage power. If we use minimum size of transistors, i.e. aspect ratio of 1, we yet again get low leakage power due to low leakage current. As a result of stacking, PMOS footer transistor will get less drain voltage.

### 6. Simulation Results

Simulation results of the circuits, given in this paper are represented by table I. These results show that the power and delay of the proposed circuit is very less among the domino logic circuits mentioned in this paper. On comparing the PDP (power-delay product) of proposed circuit with basic domino logic, footless domino logic, and footer domino logic circuits, the results of table I shows that proposed domino logic circuit has very small value of power-delay product. power delay are very important factor for improving the the capacity of a circuit in dominocircuit technology.

**Table 1:** Power, Dealy and Power Delay product Comparison of Previous and Modified Design

|                            | Basic Domino Logic | Footless Domino Logic | Footer Domino Logic | Previous Domino Logic | Modified Domino Logic |
|----------------------------|--------------------|-----------------------|---------------------|-----------------------|-----------------------|
| Supply Voltage(V)          | 1                  | 1                     | 1                   | 1                     | 1                     |
| Power(uW)                  | 13.3               | 78.4                  | 3.19                | 0.074                 | 0.056                 |
| Delay(X10 <sup>-10</sup> ) | 338                | 155                   | 103                 | 2.55                  | 0.63                  |
| PDP(X10 <sup>-19</sup> )   | 4495.4             | 1215.2                | 328.5               | 118.3                 | 35.4                  |

Table 2 represent the power-delay product of previous circuit for supply voltage of 1v, 0.9v, 0.8v, 0.7v, and 0.6v.

**Table 2** Previous Design Power Delay Product With Different Supply Voltages

| Supply Voltage(V)          | 1      | 0.9     | 0.8     | 0.7     | 0.6     |
|----------------------------|--------|---------|---------|---------|---------|
| Power(uW)                  | 0.074  | 0.059   | 0.044   | 0.030   | 0.023   |
| Delay(X10 <sup>-10</sup> ) | 2.549  | 4.129   | 9.612   | 19.793  | 33.669  |
| PDP(X10 <sup>-19</sup> )   | 188.38 | 243.831 | 414.800 | 591.410 | 773.930 |

Table 3 represents Power-delay product of previous circuit is influenced by size of transistors M6 and M7. The variation of power-delay product with the size of transistors M6 and M7 is given in table III. III.

**Table 3:** Effect of Transistor Size of M6 AND M7ON Power Delay Product

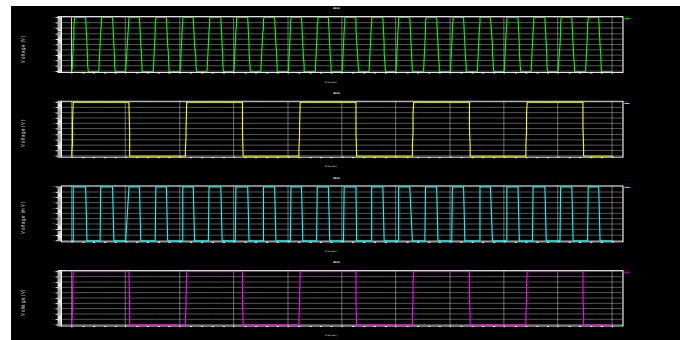
| Size of m6 & m7(nm) | 180nm | 240nm | 480nm | 500nm |
|---------------------|-------|-------|-------|-------|
| PDP (×10-19)        | 118   | 84    | 19.5  | 1.6   |

**Table 4:** Modified Design Power Dealy Product With Different Supply Voltages.

| Supply Voltage(V)          | 1     | 0.9   | 0.8   | 0.7   | 0.6   |
|----------------------------|-------|-------|-------|-------|-------|
| Power(uW)                  | 0.056 | 0.047 | 0.033 | 0.025 | 0.018 |
| Delay(X10 <sup>-10</sup> ) | 0.628 | 0.750 | 0.907 | 1.371 | 2.333 |
| PDP(X10 <sup>-19</sup> )   | 35.4  | 33.5  | 30.2  | 34.2  | 41.2  |

Results given in table IV shows that the proposed circuit gives minimum value of power-delay product for supply voltage of 1, 0.9,0.8,0.7, & on 0.6 volts. In the modified circuit of domino logic contains the stack of PMOS transistor in footer logic, the schematic and configuration of this approach work in a manner so it can reduce the leakage to ground and indirectly reduces the power dissipation novel low-leakage-power design is described. The transistors are held in reverse body bias. This reverse body biasing increases their threshold. This increased threshold voltage results in low leakage current and hence low leakage power. As we know the leakage current is the main cause of power dissipation we have reduce the leakage power using a stack of PMOS transistor in Footer circuits. Modified circuit gives best value of power-delay production with the help of reverse body bias. As we know that static power is relative to the voltage apply, through the reduced voltage the power decreases and we get the advantage of less degradation of logic

### 7. Output Waveform of Various Circuit



**Figure 5:** (a) Basic domino logic circuit

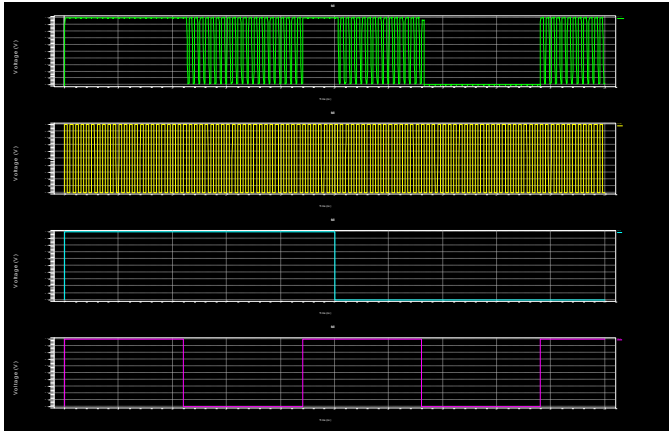


Figure 5: (b) footless domino logic circuit

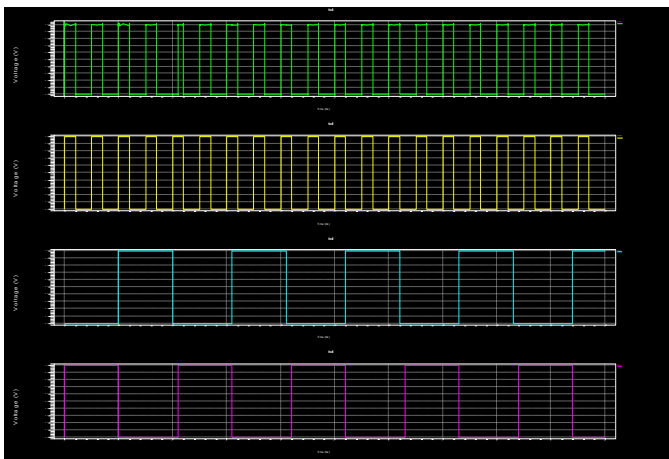


Figure 5: (c) Footer domino logic circuit

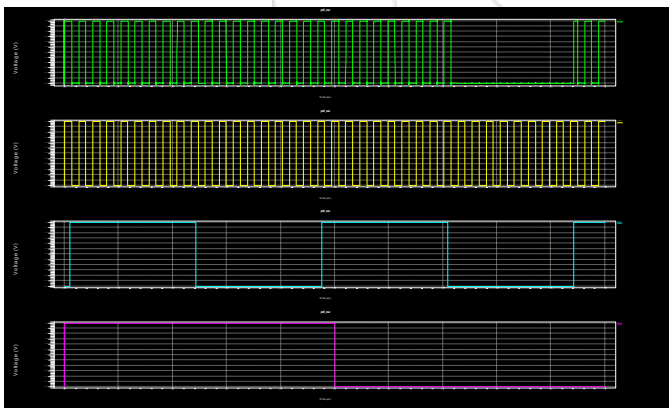


Figure 5: (d) Previous domino logic circuit



Figure 5: (e) Modified circuit using PMOS Stack in footer circuit

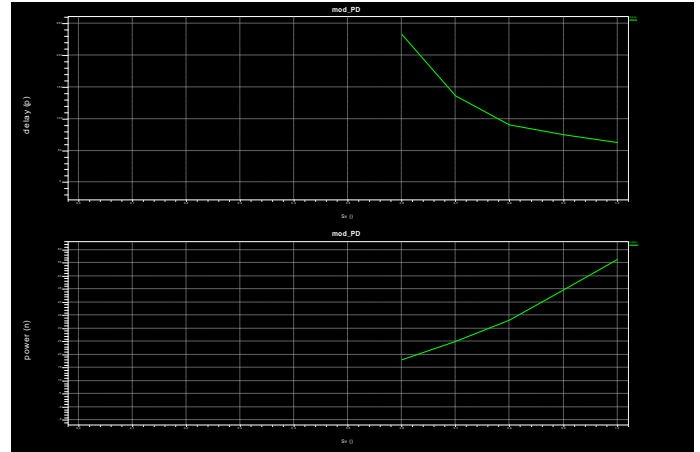


Figure 5: (f) Modified Design Power and Delay for different supply voltages

## 8. Conclusion

In this paper a new domino logic contains the stack of PMOS transistor in footer logic, the schematic and configuration of this approach work in a manner so it can reduce the leakage to ground and indirectly reduces the power dissipation novel low-leakage-power design is described. The proposed circuit is simulated on tanner tool 90nm technology. Proposed circuit when compared to previous domino logic scheme, shows reduction in speed-power product, as well as improved noise immunity. The proposed scheme is used in recent embedded processors where low power and high speed is required.

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